

January 2012

FGA30S120P Shorted Anode™ IGBT

Features

- · High speed switching
- Low saturation voltage: $V_{CE(sat)} = 1.75V @ I_C = 30A$
- · High input impedance
- · RoHS compliant

Applications

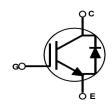
- Induction Heating and Microwave Oven
- · Soft switching Application



General Description

Using advanced Field Stop Trench and ShortedAnode technology, Fairchild's Shorted AnodeTM Trench IGBTs offer superior conduction and switching performances, and easy parallel operation with exceptional avalanche capability. This device is designed for Induction Heating and Microwave Oven.





Absolute Maximum Ratings T_C = 25°C unless otherwise noted

Symbol	Description		Ratings	Units	
V _{CES}	Collector to Emitter Voltage		1300	V	
V _{GES}	Gate to Emitter Voltage		±25	V	
Ic	Collector Current	@ T _C = 25°C	60	А	
	Collector Current	@ T _C = 100°C	30	A	
I _{CM (1)}	Pulsed Collector Current		90	А	
I _F	Diode Continuous Forward Current	@ T _C = 25°C	60	А	
l _F	Diode Continuous Forward Current	@ T _C = 100°C	30	А	
P _D	Maximum Power Dissipation	@ T _C = 25°C	348	W	
	Maximum Power Dissipation	@ T _C = 100°C	174	W	
T _J	Operating Junction Temperature		-55 to +175	°C	
T _{stg}	Storage Temperature Range		-55 to +175	°C	
T _L	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds		300	°C	

Thermal Characteristics

Symbol	Parameter	Тур.	Max.	Units	
$R_{\theta JC}(IGBT)$	Thermal Resistance, Junction to Case		0.43	°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient		40	°C/W	

Notes:

1: Limited by Tjmax

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity	
FGA30S120P	FGA30S120P	TO-3PN	=	=	30	

Electrical Characteristics of the IGBT T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Units
Off Charac	teristics					
I _{CES}	Collector Cut-Off Current	V _{CE} = 1300, V _{GE} = 0V		-	1	mA
I _{GES}	G-E Leakage Current	V _{GE} = V _{GES} , V _{CE} = 0V	-	-	±500	nA
On Charac	teristics				l	
V _{GE(th)}	G-E Threshold Voltage	I _C = 30mA, V _{CE} = V _{GE}	4.5	6.0	7.5	V
* GE(th)	Collector to Emitter Saturation Voltage	I _C = 30A, V _{GE} = 15V T _C = 25°C	-	1.75	2.3	V
V _{CE(sat)}		I _C = 30A, V _{GE} = 15V, T _C = 125°C	-	1.85	-	٧
		I _C = 30A, V _{GE} = 15V, T _C = 175°C	-	1.9		V
V _{FM}	Diode Forward Voltage	I _F = 30A, T _C = 25°C	-	1.7	2.2	V
1 IVI		I _F = 30A, T _C = 175°C	-	2.1	-	V
Dvnamic C	haracteristics		1	•	•	
C _{ies}	Input Capacitance		-	3345	4450	pF
C _{oes}	Output Capacitance	$V_{CE} = 30V_{,} V_{GE} = 0V_{,}$	-	75	100	pF
C _{res}	Reverse Transfer Capacitance	f = 1MHz	-	60	90	pF
Switching	Characcteristics					
t _{d(on)}	Turn-On Delay Time		-	39	50	ns
t _r	Rise Time		-	360	465	ns
t _{d(off)}	Turn-Off Delay Time	$V_{CC} = 600V, I_{C} = 30A,$	-	620	805	ns
t_{f}	Fall Time	$R_G = 10\Omega$, $V_{GE} = 15V$, Resistive Load, $T_C = 25^{\circ}C$	-	160	210	ns
E_{on}	Turn-On Switching Loss		-	1.3	1.7	mJ
E _{off}	Turn-Off Switching Loss		-	1.22	1.6	mJ
E _{ts}	Total Switching Loss		-	2.52	3.3	mJ
$t_{d(on)}$	Turn-On Delay Time		-	38	50	ns
t _r	Rise Time	V_{CC} = 600V, I_{C} = 30A, R_{G} = 10 Ω , V_{GE} = 15V, Resistive Load, T_{C} = 175°C	-	375	490	ns
t _{d(off)}	Turn-Off Delay Time		-	635	825	ns
t _f	Fall Time		-	270	350	ns
E _{on}	Turn-On Switching Loss		-	1.59	2.05	mJ
E _{off}	Turn-Off Switching Loss		-	1.78	2.31	mJ
E _{ts}	Total Switching Loss	1	-	3.37	4.36	mJ
Qg	Total Gate Charge		-	78	115	nC
Q _{ge}	Gate to Emitter Charge	$V_{CE} = 600 \text{V}, I_{C} = 30 \text{A},$	-	4.2	6.3	nC
Q _{gc}	Gate to Collector Charge	V _{GE} = 15V	-	33.3	50	nC

Typical Performance Characteristics

Figure 1. Typical Output Characteristics

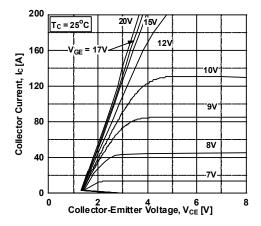


Figure 3. Typical Saturation Voltage Characteritics

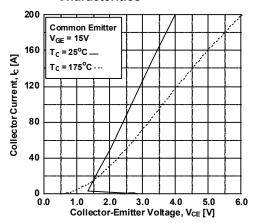


Figure 5. Saturation Voltage vs. Case

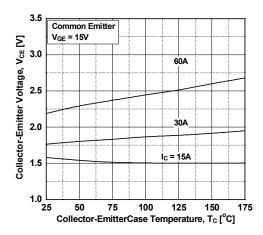


Figure 2. Typical Saturation Voltage Characteristics

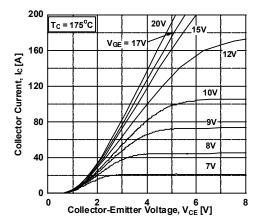


Figure 4. Transfer Characteristics

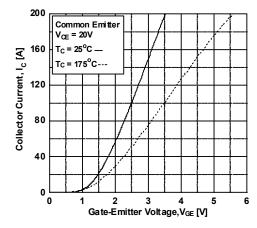
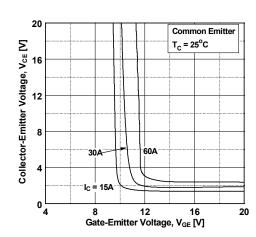


Figure 6. Saturation Voltage vs. Vge



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Typical Performance Characteristics

Figure 7. Saturation Voltage vs. Vge

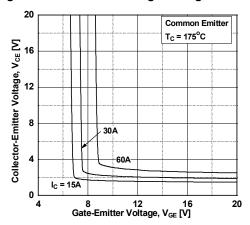


Figure 9. Gate Charge Characteristics

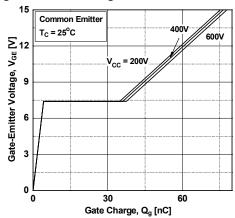


Figure 11. Turn-On Characteristics vs Gate Resistance

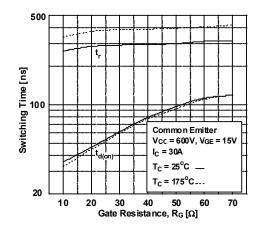


Figure 8. Capacitance Characteristics

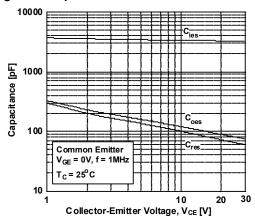


Figure 10. SOA Characteeristics

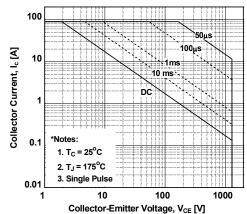
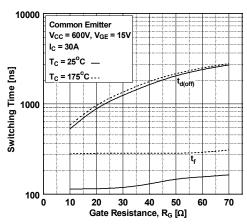


Figure 12. Turn-off Characteristics vs.
Gate Resistance



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Typical Performance Characteristics

Figure 13. Turn-on Characteristics VS. Collector Current

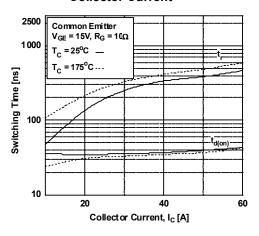


Figure 14.Turn-off Characteristics VS. Collector Current

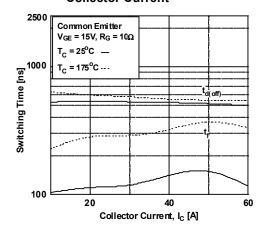


Figure 15. Switching Loss VS. Gate Resistance

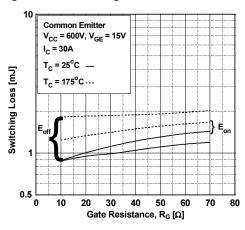


Figure 16. Switching Loss VS. Gate Resistance

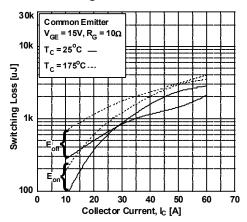


Figure 17. Turn off Switching SOA Characteristics

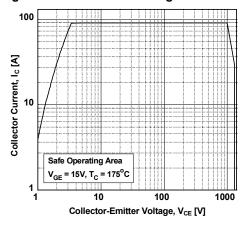
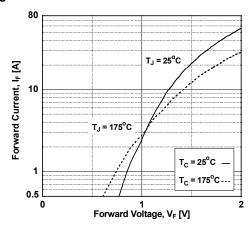


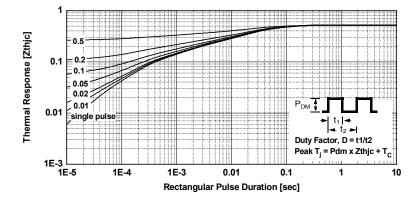
Figure 18. Forward Characteristics

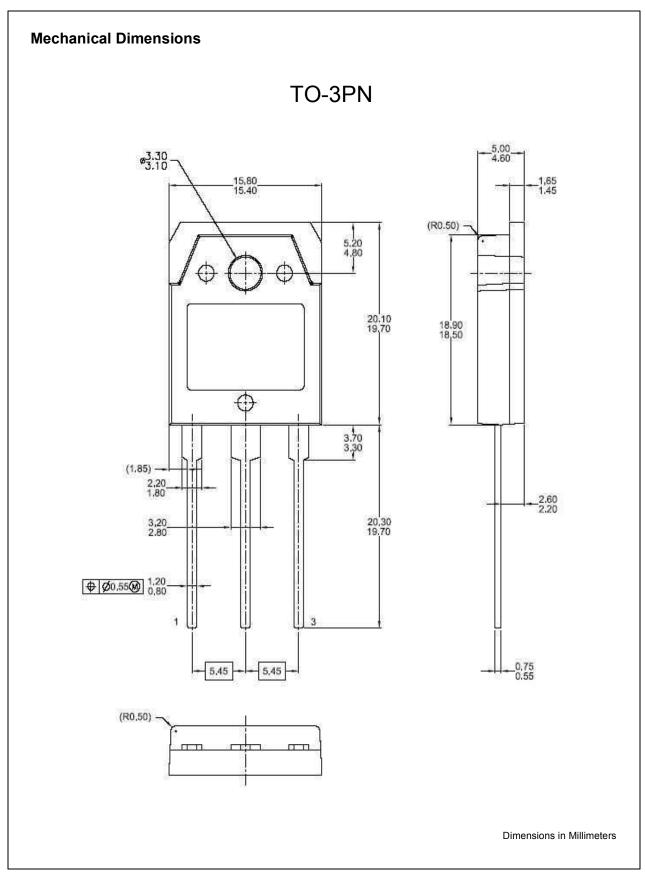


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